



Please type a plus sign (+) inside this box → +

Approved for use through 10/31/99 OMB 0651-0031

Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

PTO/SB/08A (10-96)

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

*(use as many sheets as necessary)*

Sheet	1	Of	2	Attorney Docket Number	27054
-------	---	----	---	------------------------	-------

### U.S. PATENT DOCUMENTS

Examiners Initials	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, columns, lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
NS		6,340,640		Nishimoto et al	01-22-2002	
NS		6,197,611		Nishimoto	03-06-2001	
NS		5,990,002		Niroomand et al ;	11-23-1999	
NS		5,830,793		Schuegraf et al	11-03-1998	
NS		6,091,021		Ruby et al	07-18-2000	
NS		6,096,968		Schlosser et al	08-01-2000	
NS		6,319,566		Polanyi et al	11-20-2001	
NS		6,329,296		Ruby et al	12-11-2001	
NS		6,339,013		Naseem et al	01-15-2002	
NS		6,420,647		Ji et al	07-16-2002	
NS		6,530,826		Wenski	03-11-2003	
NS		6,127,623		Nakamura et al	10-03-2000	
NS		5,081,049		Green et al	01-14-1992	
NS		4,131,488		Lesk et al	12-26-1978	
NS		4,229,233		Hansen et al	10-21-1980	
NS		4,571,448		Barnett	02-18-1986	
NS		4,818,337		Barnett et al	04-04-1989	
NS		5,030,295		Swanson et al	0709-1991	
NS		5,627,081		Tsuo et al	05-06-1977	
NS		5,702,538		Endros et al	12-30-1997	
NS		5,792,280		Ruby et al	08-11-1998	
NS		6,156,968		Nishimoto et al	12-05-2000	
NS		6,391,145		Nishimoto et al	05-21-2002	
NS		6,555,443		Artnmann et al	04-29-2003	
NS		6,602,767		Nishida et al	08-05-2003	
NS		6,613,653		Naseem et al	09-02-2003	
NS		6,521,118		Starosvetsky et al	02-18-2003	

### FOREIGN PATENT DOCUMENTS

Examiners Initials	Cite No. <sup>1</sup>	Foreign Patent Documents			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, columns, lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				

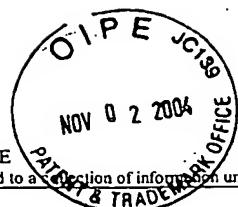
Examiner Signature /Nicholas Smith/ Date Considered 05/08/2007

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, Patent and Trademark Office, Washington, DC 20231.

DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.



Please type a plus sign (+) inside this box →

Approved for use through 10/31/99 OMB 0651-0031

Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

PTO/SB/08A (10-96)

Substitute for form 1449A/PTO

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known	
Application Number	10/750,969
Filing Date	01/05/2004
First Named Inventor	Ein-Eli
Group Art Unit	1742
Examiner Name	

Sheet	2	Of	2	Attorney Docket Number	27054
<b>OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS</b>					
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.			T <sup>2</sup>
NS		Ein-Eli et al, "Silicon Texturing Under Negative Potential Dissolution (NPD)", <i>Int. Soc. Electrochemistry</i> , Ann. Mtg., Thessaloniki, 19-24-Sept., 2004			
NS		Ein-Eli et al, " Silicon Texturing In Alkaline Media Conducted Under Extreme Negative Potentials", <i>Electrochem. &amp; Solid State Letters</i> , 6(3):C47-C50, 2003			
NS		Starosvetsky et al, "Environmentaly Friendly, Fast Electrochemical Etching of Silicon", <i>Electrochemical Society Proceedings</i> , Proceedings Vol. 2002-14, pp 286-299			
NS		Zhang GZ, "Electrochemistry of Silicon and Its Oxide", Kluwer Academic Pub, August 2001, pp 279-339			
NS		Sidell et al, "Anisotropic Etchings of Crystalline Silicon in Alkaline Solutions", <i>J. Electrochem Soc.</i> , 137(11): 3612-3626, 1990			
NS		Kwa et al, " Anisotropically Etched Silicon Mirrors for Optical Sensor Applications", <i>J. Electrochem Soc.</i> , 142(4): 1226-1233, 1995			
NS		Vu et al, "Surface Characteristics of (100) Silicon Anisotrpically Etched in Aqueous KOH", <i>J. Electrochem Soc.</i> , 143(4): 1372-1375, 1996			
NS		Zhong etal, "Porous Silicon Formation and Electropolishing of Silicon by Anodic Polarization in HF Solution", <i>J. Electrochem Soc.</i> , 136(5): 1561-1565, 1989			
NS		Allongue et al, "Etching of Silicon in NaOH Solutions", <i>J. Electrochem Soc.</i> , 140(4): 1009-1018, 1993			
NS		Glembocski et al, "Bias-Dependent Etching of Silicon in Aqueous KOH", <i>J. Electrochem Soc.</i> , 132(1): 145-151, 1985			
NS		Tellier et al, "Anisotropic Etching of Silicon Crystals in KOH Solution ", <i>J. Material Science</i> , 29:5953-5971, 1994			
NS		Green et al, "45% Efficient Silicon Photovoltaic Cell Under Monochromatic Light", <i>IEEE Electron Device Letters</i> , 13(6):317,318, 1992			
NS		Vazsonyi et al, "Improved Anisotropic Etching Process for Industrial Texturing of Silicon Solar Cells", <i>Solar Energy Materials &amp; Solar Cells</i> , 57:179-188, 1999			
NS		Wovte et al, "Grid-Connected Photovoltaic Systems", <i>International conference Power Generation and sustainable development (AIM)</i> , Liège, Belgium, October 8-9, 2001; pp. 233-238.			
NS		Nijs et al, "Crystalline Silicon Solar Cells Technology for Today and Tomorrow », Proc. Of the 16 <sup>th</sup> European Photovoltaic Solar Energy Conference, Glasgow, 2000			
NS		Ein-Eli et al, Suppresion of Zinc-Anode Corrosion in Alkaline Solutions with the Use of Organic Inhibitors", 202 <sup>nd</sup> Meeting of the Electrochemical Society, Salt Lake City, Utah, 200s, Abstarct 344			
NS		Sato et al, "Roughening of Single-Crystal Silicon Surface Etched by KOH Water Solution", <i>Sensors and Actuators</i> , 73:122-130, 1999			
Examiner Signature	/Nicholas Smith/			Date Considered	05/08/2007

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>. Unique citation designation number. <sup>2</sup>. Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, Patent and Trademark Office, Washington, DC 20231.

DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.